NSN 5962-01-506-3280

Memory Microcircuit - Page 1 of 1



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| Maximum Power Dissipation Rating: |
|--|
| 1.5 watts |
| |
| Operating Tempurature Range: |
| -40.0/+85.0 degrees celsius |
| End Application: |
| Used in 114e6472g1 |
| Features Provided: |
| Electrically alterable and programmable |
| Inclosure Material: |
| Ceramic |
| Inclosure Configuration: |
| Leaded chip carrier |
| Output Logic Form: |
| Complementary-metal oxide-semiconductor logic |
| Input Circuit Pattern: |
| 22 input |
| Terminal Surface Treatment: |
| Solder |
| Product Name: |
| Micrcocicuit, memory, digital, cmos, ee programmable array logic, monolithic silicon |
| Voltage Rating And Type Per Characteristic: |
| -0.5 volts total supply and 7.0 volts total supply |
| Time Rating Per Chacteristic: |
| 15.00 nanoseconds af output megawatts |
| Memory Device Type: |
| Pal |
| Hybrid Technology Type: |
| Monolithic |
| Special Features: |
| Use program 356a1289p3.Jed to program 356a1409p16 or atf22v10bq-15jc |
| Terminal Type And Quantity: |
| 28 j-hook |
| Shelf Life: |
| N/a |
| Unit Of Measure: |
| |
| Demilitarization: |
| No |
| Fiig: |
| A458a0 |